

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A manufacturing method of an SOI wafer, comprising:
preparing a supporting wafer comprising boron in an amount of 9×10^{18} atoms/cm³ or more;
forming ~~a rear surface~~ an insulating film having a thickness of 0.1-0.5 μ m on at least a surface opposite to a bonding surface on one surface of said supporting wafer;
ion-implanting hydrogen gas or a noble gas element to an active layer wafer to thereby form an ion-implanted layer in said active layer wafer;
bonding said active layer wafer with a the other surface of said supporting wafer via an insulating film interposed therebetween to thereby form a bonded wafer; and then heat treating said bonded wafer to thereby induce cleavage in a portion of said bonded wafer at the site of the ion-implanted layer as an interface to thereby form an SOI layer with said remaining active layer wafer for manufacturing said SOI wafer.
2. (Cancelled)
3. (Previously Presented) A manufacturing method of an SOI wafer in accordance with claim 1, wherein a thickness of the SOI layer is less than 0.10 μ m.
- 4 - 21. (Cancelled)